Rapid Thermal Processing of Electronic Materials

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Contents

PREFACE xix

PART I: INTRODUCTION

RAPID THERMAL PROCESSING: HOW WELL IS IT DOING AND WHERE IS IT GOING? 3
T.O. Sedgwick

PART II: ION IMPLANTATION, DOPANT ACTIVATION AND DIFFUSION

DOPANT INCORPORATION OF BORON IMPLANTED SILICON DURING RAPID THERMAL ANNEALING 15
Hung-Yu Liu, Peng-Heng Chang, Jiann Liu, and Bor-Yen Mao

PROPERTIES OF HIGH DOSE LOW TEMPERATURE RAPID THERMALLY ANNEALED GALLIUM IMPLANTED SILICON 21

A STUDY OF DIFFUSION, CLUSTERING AND DEFECTS IN AS+ AND BF2+ IMPLANTED SILICON DURING SCANNING ELECTRON BEAM ANNEALING 27
Michael J. Hart, Alan G.R. Evans, Gehan A.J. Amaratunga, and John L. Altrip

ENHANCED DIFFUSION DURING RAPID THERMAL ANNEALING OF INDIUM AND BORON IN DOUBLE IMPLANTED SILICON 33
E. Ganin, G.A. Sai-Halasz, and T.O. Sedgwick

NUCLEAR REACTION ANALYSIS OF SHALLOW B AND BF2 IMPLANTS IN Si 39
Mark C. Ridgway, P.J. Scanlon, and J.L. Whitton

THE REDISTRIBUTION OF IMPURITIES UNDER RTP FOR POLYSILICON CAPPED SILICON 41
R.S. Hockett

EPITAXIAL ALIGNMENT OF AS IMPLANTED POLYSILICON EMITTERS 47
J.L. Hoyt, E.F. Crabbé, J.F. Gibbons, and R.F.W. Pease

DRIFT OF ARSENIC IN SiO2 IN A LAMP FURNACE WITH A BUILT-IN TEMPERATURE GRADIENT 53

APPLICATIONS OF PULSED CO2 LASER PROCESSING OF SILICON 59
R.B. James

*Invited Paper
CHARACTERIZATION OF SHALLOW JUNCTIONS FABRICATED BY GAS IMMERSION LASER DOPING (GILD)


PART III: DIELECTRICS, RAPID THERMAL OXIDATION, RAPID THERMAL NITRIDATION

RAPID THERMAL/PLASMA PROCESSING FOR IN-SITU DIELECTRIC ENGINEERING

Mehrdad M. Moslehi

RAPID THERMAL ANNEALING OF LOW TEMPERATURE SILICON DIOXIDE FILMS

J.T. Fitch and G. Lucovsky

PROCESS AND EQUIPMENT ISSUES IN RAPID THERMAL OXIDATION (RTO)

Sandeep Mehta and David Hodul

KINETICS OF RAPID THERMAL OXIDATION OF SILICON

Stephan E. Lassig, Thomas J. DeBoiske, and John L. Crowley

CHARACTERISTICS OF THIN LAYERS OF SiO₂ FABRICATED BY RAPID THERMAL OXIDATION

S. Prasad, J. Haase, R. Früchtnicht, R. Ferretti, and D. Haack

A COMPARISON OF RTO AND FURNACE OXIDES

Marie E. Burnham, Ronald N. Legge, Jaim Nulman, Peter L. Fejes, and James F. Brown

RAPID THERMAL NITRIDATION OF THIN OXIDES


RAPID THERMAL PROCESSING OF GATE DIELECTRIC FILMS AND THEIR CHARACTERIZATION

D.L. Flowers, J. Nulman, and J.P. Krusius

COMPARISON OF THE GROWTH KINETICS OF OXIDES GROWN IN TUNGSTEN-HALOGEN AND WATER COOLED ARC LAMP SYSTEMS

C.A. Paz de Araujo, J.C. Gelpey, Y.P. Huang, and R. Kwor

IN-SITU PROCESSING OF SILICON DIELECTRICS BY RAPID THERMAL PROCESSING: CLEANING, GROWTH, AND ANNEALING

J. Nulman

OXIDATION OF SILICON AND NITRIDATION OF SiO₂ BY RAPID THERMAL PROCESSES

N. Chan Tung, Y. Caratini, and J.L. Buevoz

*Invited Paper
PART IV: SILICIDES AND METALS

*RAPID THERMAL PROCESSING FOR SELF-ALIGNED SILICIDE TECHNOLOGY

EFFECTS OF TiSi₂/TiN/Al CONTACT METALLIZATION PROCESS ON THE SHALLOW JUNCTION RELATED PROPERTIES
  S.W. Sun, F. Pintchovski, P.J. Tobin, and R.L. Hance

LOW TEMPERATURE RAPID THERMAL FORMATION OF TiN BARRIER LAYERS
  Barney Cohen and Jaim Nulman

RESISTIVITY DIFFERENCES IN C49 TiSi₂ FILMS FORMED BY RAPID THERMAL PROCESSING
  A.H. Reader, A.H. van Ommen, and H.J.W. van Houtum

CHARACTERIZATION OF PROCESS UNIFORMITY AND CONTROL OF TITANIUM SILICIDE FORMED BY RAPID THERMAL PROCESSING (RTP)
  David Hodul and Sandeep Mehta

HIGH PURITY TITANIUM SILICIDE FILMS FORMED BY SPUTTER DEPOSITION AND RAPID THERMAL ANNEALING
  T. Brat, J.C.S. Wei, J. Poole, D. Hodul, N. Parikh, and C. Wickersham, Jr.

SHALLOW JUNCTION FORMATION BY THE REDISTRIBUTION OF SPECIES IMPLANTED INTO COBALT SILICIDE
  Brian M. Ditchek, Marvin Tabasky, and Emel S. Bulat

COMPARISONS OF SILICIDE FORMATION BY RAPID THERMAL ANNEALING AND CONVENTIONAL FURNACE ANNEALING
  E. Ma, M. Natan, B.S. Lim, and M-A. Nicolet

RAMAN SCATTERING FROM RAPID THERMALLY ANNEALED TUNGSTEN SILICIDE
  Sanhita Dasgupta, Sandeep Kumar, Howard E. Jackson, and Joseph T. Boyd

PART V: RAPID THERMAL PROCESSING OF DEVICES AND CIRCUITS

APPLICATION OF RTA TO BIPOLAR IC'S
  Robert H. Reuss and Thomas P. Bushey

CONTROL OF BIPOLAR JUNCTION TRANSISTOR CURRENT GAIN USING RAPID THERMAL PROCESSING
  A. Kermani, P. Van Gieson, S. Litwin, R. Sullivan, T.J. DeBolske, and J.L. Crowley

*Invited Paper
THE EFFECT OF RAPID THERMAL PROCESSING ON THE ELECTRICAL CHARACTERISTICS OF POLYSILICON GATE MOS CAPACITORS
Susan B. Felch, David T. Hodul, and Mak Salimian

AN ELECTRICAL CHARACTERIZATION OF SOI FILMS USING DEVICES FORMED BY OXYGEN IMPLANT AND RAPID THERMAL PROCESSING
Jim D. Whitfield, Marie E. Burnham, Charles J. Varker, and Syd R. Wilson

PART VI: RECENT DEVELOPMENTS IN RTP EQUIPMENT

*RAPID THERMAL PROCESSING--A USER'S PERSPECTIVE
R.T. Fulks

SILICON TEMPERATURE AND THERMAL GRADIENTS MEASUREMENTS IN A RAPID THERMAL PROCESSOR OPERATING AT ATMOSPHERIC PRESSURE OR IN VACUUM
J-M. Dilhac, C. Ganibal, and A. Martinez

SLIP FREE RAPID THERMAL PROCESSING
Julian Blake, Jeffrey C. Gelpey, John F. Moquin, James Schlueter, and Ron Capodilupo

A METHOD FOR RAPID THERMAL ANNEALING OF COMPOUND SEMICONDUCTORS BY CW CO₂ LASER IRRADIATION
U. Neta, V. Richter, and R. Kalish

PART VII: NEW APPLICATIONS OF RTP

*LIMITED REACTION PROCESSING: SILICON AND III-V MATERIALS

MICROWAVE PLASMA LPCVD OF TUNGSTEN IN A COLD-WALL LAMP-HEATED RAPID THERMAL PROCESSOR
Mehrdad M. Moslehi, Krishna C. Saraswat, and Steven C. Shatas

LIMITED REACTION PROCESSING: GROWTH OF III-V EPITAXIAL LAYERS BY RAPID THERMAL METALORGANIC CHEMICAL VAPOR DEPOSITION
S. Reynolds, D.W. Vook, and J.F. Gibbons

RAPID THERMAL ANNEALING OF AMORPHOUS HYDROGENATED CARBON (a-C:H) FILMS
Samuel A. Alterovitz, John J. Pouch, and Joseph D. Warner

*Invited Paper
PART VIII: DEFECTS AND MICROSTRUCTURE IN RTP MATERIALS

*DEFECT STRUCTURES AND ELECTRICAL BEHAVIOR OF RAPID THERMALLY ANNEALED ION IMPLANTED SILICON
D.K. Sadana

PROPERTIES OF GALLIUM IMPLANTED FURNACE AND RAPIDLY ANNEALED POLYCRYSTALLINE SILICON
H.B. Harrison, A.P. Pogany, and Y. Komem

SECONDARY GRAIN GROWTH DURING RAPID THERMAL ANNEALING OF DOPED POLYSILICON FILMS
R.C. Cammarata, C.V. Thompson, and S.M. Garrison

RAPID THERMAL ANNEALING OF OXYGEN-VACANCY CENTERS IN O-IMPLANTED SILICON
H.J. Stein

THE EFFECT OF RAPID THERMAL TREATMENT ON THE STRUCTURAL AND OPTOELECTRONIC PROPERTIES OF EPITAXIAL GaAs ON Si GROWN WITH OR WITHOUT Ge INTERMEDIATE LAYERS

POINT DEFECT EVOLUTION DURING RAPID THERMAL ANNEALING OF Si⁺-IMPLANTED GaAs
M. Levinson, C.A. Armiento, and S.S.P. Shah

PART IX: THE EFFECTS OF RTP ON DEFECTS, CONTACTS, AND EPITAXIAL LAYERS OF COMPOUND SEMICONDUCTORS

RAPID-THERMAL-PROCESSING INDUCED DEEP LEVEL TRAPS AND THEIR SPATIAL DISTRIBUTION IN MBE GaAs
Akio Kitagawa, Yutaka Tokuda, Akira Usami, Takao Wada, and Hirooyuki Kano

FORMATION OF p⁺ AND HIGH RESISTIVITY REGIONS IN GaAs-AlGaAs HETEROJUNCTIONS
S.J. Pearton, J.M. Brown, and K.T. Short

ELECTRICAL PROPERTIES OF n- AND p-TYPE In₀.₅₃Ga₀.₄₇As LAYERS FORMED BY ION IMPLANTATION AND RAPID THERMAL (FLASH) ANNEAL

THERMAL STABILITY OF TaSiₓ-GaAs SCHOTTKY BARRIERS
T.E. Haynes, C.C. Han, S.S. Lau, S.T. Picraux, and W.K. Chu

RAMAN SCATTERING STUDY OF THE Au-Ge-GaAs OHMIC CONTACT STRUCTURE FORMED BY RAPID THERMAL PROCESSING
D. Kirillov and Y. Chung

*Invited Paper
DIFFUSION OF Zn INTO GaAs$_{0.6}$P$_{0.4}$:Te FROM Zn-DOPED OXIDE FILMS BY RAPID THERMAL PROCESSING
A. Usami, Y. Tokuda, H. Shiraki, H. Ueda, T. Wada, H. Kan, and T. Murakami

PART X: THE EFFECTS OF RTP ON ION IMPLANTATION AND DIFFUSION IN COMPOUND SEMICONDUCTORS

*RAPID THERMAL PROCESSING FOR HIGH-SPEED III-V COMPOUND DEVICES
M. Kuzuhara

CO-IMPLANTATION OF Si AND Be IN GaAs BY RAPID THERMAL ANNEALING
Tan-Hua Yu and Sujane Wang

RAPID THERMAL PROCESSING OF SILICON ION IMPLANTED CHANNEL LAYERS IN GaAs
Tohru Hara and Jeffrey C. Gelpey

FORMATION OF DEVICE QUALITY p-TYPE LAYERS IN GaAs USING CO-IMPLANTATION OF Mg$^+$ AND As$^+$ AND CAPLESS RAPID THERMAL ANNEALING
A.N.M. Masum Choudhury and C.A. Armiento

RAPID THERMAL ANNEALING OF Se-IMPLANTED GALLIUM ARSENIDE
T. Inada, K. Miyamoto, and A. Nishida

Si IMPLANTS INTO PREAMORPHISED GaAs
R. Gwilliam, R.S. Deol, R. Blunt, and B.J. Sealy

CARRIER AND ATOMIC DISTRIBUTIONS IN Si IMPLANTED AND RAPID THERMALLY ANNEALED InP: INFLUENCE OF DUAL IMPLANTS OF As OR P
Nicole Duhamel, Brigitte Descouts, Philippe Krauz, Krishna Rao, Jean Dangla, and Pierre Henoc

RAPID THERMAL ANNEALING OF HIGH ENERGY Si IMPLANTS INTO GaAs
Ronald N. Legge and Wayne M. Paulson

ANNEAL BEHAVIOR OF Zn IMPLANTED InP: FURNACE AND RAPID THERMAL ANNEALS
M. Djamei, E.V.K. Rao, and P. Krauz

RAPID THERMAL DIFFUSION OF ZINC IN GaAs
T.S. Kalkur, Y.C. Lu, C.A. Paz de Araujo

TUNGSTEN SILICIDE ZINC AS A HIGH TEMPERATURE ZINC DIFFUSION SOURCE
D.L. Plumton

A TWO STEP RAPID THERMAL ANNEALING PROCESS FOR Be IMPLANT ACTIVATION IN GaAs
D.L. Plumton, W.M. Duncan, and L.T. Tran

*Invited Paper
AUTHOR INDEX 481

SUBJECT INDEX 483